

SVKM'S NMIMS STME, Navi-Mumbai Campus
FE CSBS Sem II
PEE : Graded Assignment 3
Max. Marks : 5

Last date of submission for written assignment: March 20, 2020

Instruction: 2M for punctual submission + 3M for neat diagrams and clear explanation. Zero marks for delayed submission.

- Q1. Compare BJT and FET (Some points: Diagram, charge carriers involved, applications, control/controlled parameters etc.)
- Q2. Draw the construction of the following devices. Also explain the working and characteristics
- JFET (either p-channel or n-channel)
 - Enhancement MOSFET (either p-channel or n-channel)
 - Depletion MOSFET (either p-channel or n-channel)
- Q3. Explain the concept of CMOS (Complementary MOS- can explain working of CMOS inverter)

Refer Chapter 5 Boylestad